

PRELIMINARY

Notice : This is not a final specification
Some parametric limits are subject to change.

MITSUBISHI SEMICONDUCTOR <GaAs MMIC>

MGFC5213

K-Band 2-Stage Power Amplifier

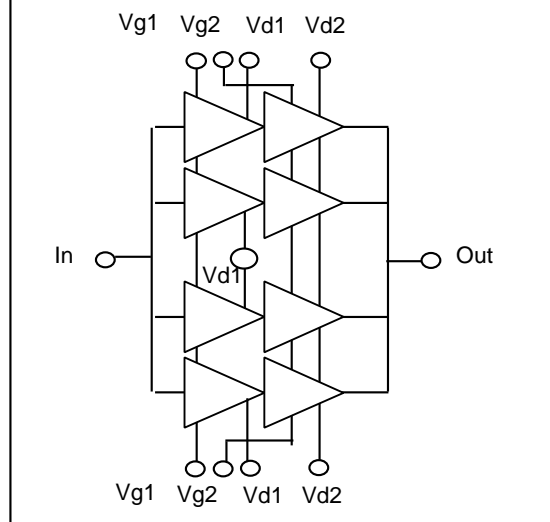
DESCRIPTION

The MGFC5213 is a GaAs MMIC chip especially designed for 27.5 ~ 30.0 GHz band High Power Amplifier (HPA) .

FEATURES

- RF frequency : 27.5 to 30.0 GHz
- Linear gain : 9 dB
- P1dB : 29 dBm
- DC power : $V_d = 5\text{ V}$, $I_{d1} + I_{d2} = 1080\text{ mA}$

BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

Symbol	Parameter	Ratings	Units
Vd1, Vd2	Drain supply voltage	6	V
Vg1, Vg2	Gate supply voltage	-3 ~ 0.5	V
Id1	Drain current 1	480	mA
Id2	Drain current 2	960	mA
Pin	RF input power	25	dBm
Ta	Backside ambient temp.	-20 ~ +70	°C
Tstg	Storage temp.	-65 ~ +175	°C
Tmax	Maximum assembly temp.	+300	°C

ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

Symbol	Parameter	Conditions	Limits			Units
			Min.	Typ.	Max.	
Gain	Gain	Vd = 5 V Id1 = 360 mA Id2 = 720 mA (RF off)	9.0			dB
VSWR in	Input VSWR				3.0	-
VSWR out	Output VSWR				3.0	-
P1dB	Output power at 1 dB compression point	f = 27.5, 30.0 GHz Single tone	29.0			dBm

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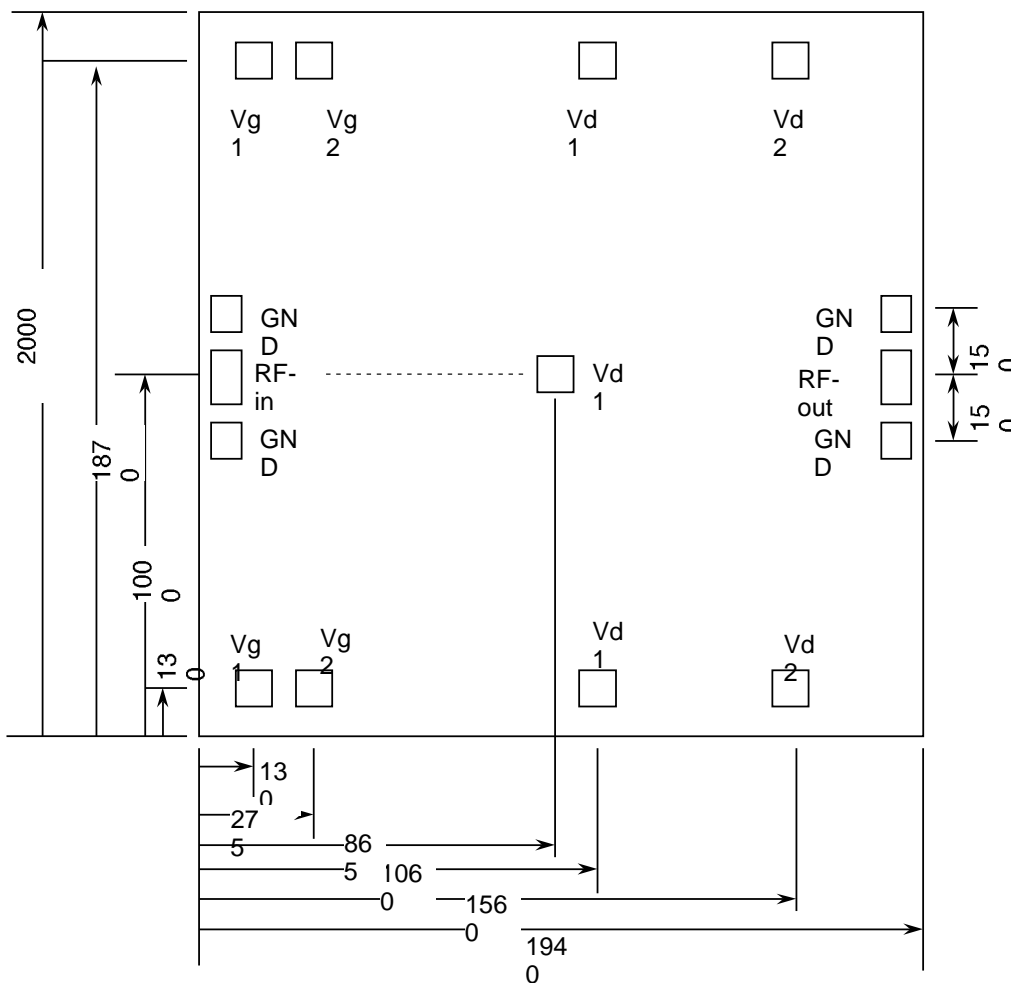
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DIE SIZE AND BOND PAD LOCATION(UNIT : μM)



X Dimention 1.94 mm
Y Dimention 2.00 mm

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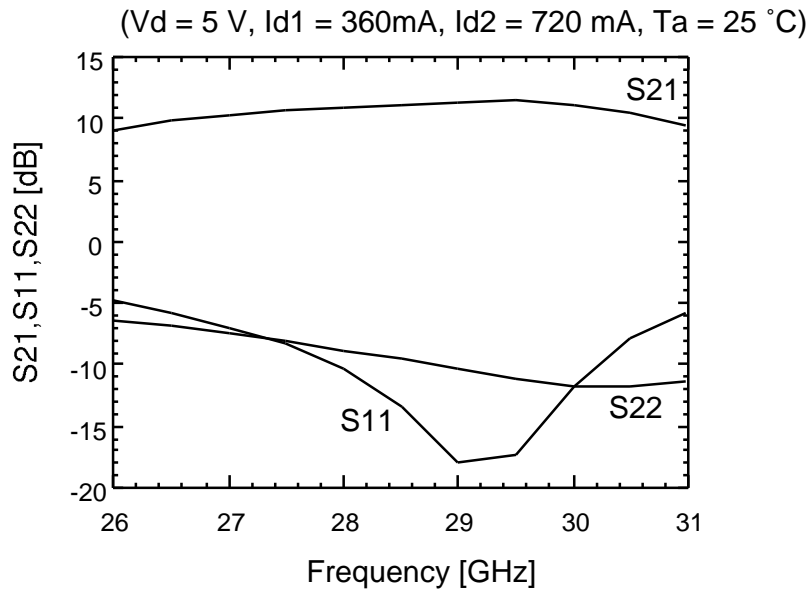
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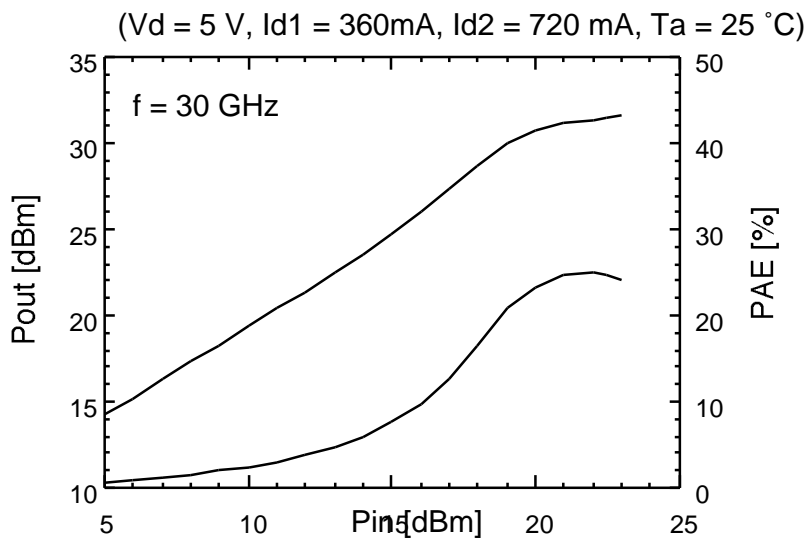
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TYPICAL CHARACTERISTICS

Small Signal Performances



Output Power Performances



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AN EXAMPLE OF TEST CIRCUIT

